

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	54	("ILD" or "interlevel dielectric") and etch\$4 and (open or via or hole or trench) and (semiconductor or wafer or substrate) and (inert near gas) and cap and liner	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/15 12:12
S2	0	("ILD" or "interlevel dielectric") and etch\$4 and (open or via or hole or trench) and (semiconductor or wafer or substrate) and (inert near gas) and cap and liner and chamber and "metal layer" and ("tantalum nitride" or "TaN") and depositon and argon and nitrogen	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 10:55
S3	0	("ILD" or "interlevel dielectric") and etch\$4 and (open or via or hole or trench) and (semiconductor or wafer or substrate) and (inert near gas) and cap and liner and chamber and metal and ("tantalum nitride" or "TaN") and depositon and argon and nitrogen	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 10:55
S4	35	("ILD" or "interlevel dielectric") and etch\$4 and (open or via or hole or trench) and (semiconductor or wafer or substrate) and (inert near gas) and cap and liner and chamber and metal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 10:55
S5	15	("ILD" or "interlevel dielectric") and etch\$4 and (open or via or hole or trench) and (semiconductor or wafer or substrate) and (inert near gas) and cap and liner and chamber and metal and "tantalum nitride"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 10:55
S6	4	("ILD" or "interlevel dielectric") and etch\$4 and (open or via or hole or trench) and (semiconductor or wafer or substrate) and (inert near gas) and cap and liner and chamber and metal and "tantalum nitride" and argon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 10:55

S7	2	("ILD" or "interlevel dielectric") and etch\$4 and (open or via or hole or trench) and (semiconductor or wafer or substrate) and (inert near gas) and cap and liner and chamber and metal and "tantalum nitride" and (argon near4 nitrogen)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 10:56
S8	2	("ILD" or "interlevel dielectric") and etch\$4 and (open or via or hole or trench) and (semiconductor or wafer or substrate) and (inert near gas) and cap and liner and chamber and metal and "tantalum nitride" and (argon near4 nitrogen) and deposit\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 12:41
S9	0	("ILD" or "interlevel dielectric") and etch\$4 and (open or via or hole or trench) and (semiconductor or wafer or substrate) and (inert near gas) and cap and liner and degass	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 12:42
S10	0	("ILD" or "interlevel dielectric") and etch\$4 and (open or via or hole or trench) and (semiconductor or wafer or substrate) and (inert near gas) and degass	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 12:42
S11	4	("ILD" or "interlevel dielectric") and etch\$4 and (open or via or hole or trench) and (semiconductor or wafer or substrate) and (inert near gas) and degas	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 12:42
S12	531	"ILD" and etch and cap and (semiconductor or wafer or substrate) and barrier	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/15 12:14
S13	462	"ILD" and etch and cap and (semiconductor or wafer or substrate) and barrier and via	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/15 12:14
S14	63	"ILD" and etch and cap and (semiconductor or wafer or substrate) and barrier and via and argon and nitrogen	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/15 12:14

S15	0	"ILD" and etch and cap and (semiconductor or wafer or substrate) and barrier and via and argon and nitrogen and chamber and degas	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/15 12:14
S16	27	"ILD" and etch and cap and (semiconductor or wafer or substrate) and barrier and via and argon and nitrogen and chamber and ("TaN" or "tantalum nitride") and (metal or conduct\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/15 12:18
S17	0	"ILD" and etch and cap and (semiconductor or wafer or substrate) and barrier and via and argon and nitrogen and chamber and ("TaN" or "tantalum nitride") and (metal or conduct\$4) and degas	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/15 12:19
S18	27	"ILD" and etch and cap and (semiconductor or wafer or substrate) and barrier and via and argon and nitrogen and chamber and ("TaN" or "tantalum nitride") and (metal or conduct\$4) and remov\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/15 12:19
S19	6	"ILD" and etch and cap and (semiconductor or wafer or substrate) and barrier and via and argon and nitrogen and chamber and ("TaN" or "tantalum nitride") and (metal or conduct\$4) and (remov\$4 near8 gas)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/15 12:22
S20	20	"ILD" and etch and ("SiC" or "silicon carbide" or "SiN" or "silicon nitride") and (semiconductor or wafer or substrate) and barrier and via and argon and nitrogen and chamber and ("TaN" or "tantalum nitride") and (metal or conduct\$4) and (remov\$4 near8 gas)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/15 12:23